Octal D-Type Latch with 3-State Outputs

With 5 V-Tolerant Inputs

The MC74LVX573 is an advanced high speed CMOS octal latch with 3-state outputs. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

This 8-bit D-type latch is controlled by a latch enable input and an output enable input. When the output enable input is high, the eight outputs are in a high impedance state.

Features

- High Speed: $t_{PD} = 6.4 \text{ ns}$ (Typ) at $V_{CC} = 3.3 \text{ V}$
- Low Power Dissipation: $I_{CC} = 4 \mu A$ (Max) at $T_A = 25^{\circ}C$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Low Noise: $V_{OLP} = 0.8 \text{ V (Max)}$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: Human Body Model > 2000 V;

Machine Model > 200 V

• These Devices are Pb-Free and are RoHS Compliant



ON Semiconductor®

http://onsemi.com

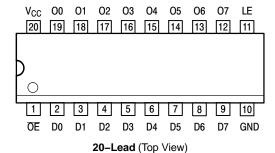




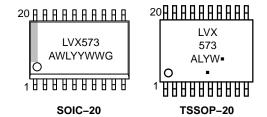


TSSOP-20 DT SUFFIX CASE 948E

PIN ASSIGNMENT



MARKING DIAGRAMS



LVX573 = Specific Device Code A = Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

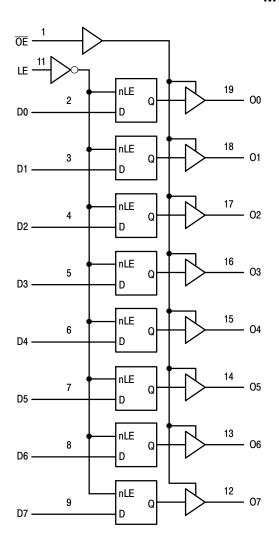


Figure 1. Logic Diagram

Table 1. PIN NAMES

Pins	Function
OE	Output Enable Input
LE	Latch Enable Input
D0-D7	Data Inputs
O0-O7	3–State Latch Outputs

I	INPUTS		OUTPUTS	
OE	LE	Dn	On	OPERATING MODE
L	ΗH	H L	H L	Transparent (Latch Disabled); Read Latch
L	∟∟	h I	H L	Latched (Latch Enabled) Read Latch
L	L	Х	NC	Hold; Read Latch
Н	L	Х	Z	Hold; Disabled Outputs
H	ΙΙ	H L	Z Z	Transparent (Latch Disabled); Disabled Outputs
H H	L L	h I	Z Z	Latched (Latch Enabled); Disabled Outputs

H = High Voltage Level; h = High Voltage Level One Setup Time Prior to the Latch Enable High–to–Low Transition; L = Low Voltage Level; l = Low Voltage Level One Setup Time Prior to the Latch Enable High–to–Low Transition; NC = No Change, State Prior to the Latch Enable High–to–Low Transition; X = High or Low Voltage Level or Transitions are Acceptable; Z = High Impedance State; For I_{CC} Reasons DO NOT FLOAT Inputs.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0	V
V _{in}	DC Input Voltage	-0.5 to +7.0	V
V _{out}	DC Output Voltage	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Diode Current	-20	mA
lok	Output Diode Current	±20	mA
l _{out}	DC Output Current, per Pin	±25	mA
Icc	DC Supply Current, V _{CC} and GND Pins	±75	mA
P _D	Power Dissipation	180	mW
T _{stg}	Storage Temperature	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	3.6	V
V _{in}	DC Input Voltage	0	5.5	V
V _{out}	DC Output Voltage	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	-40	+85	°C
Δt/ΔV	Input Rise and Fall Time	0	100	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			Vcc	Т	A = 25°	С	$T_A = -40$	to 85°C	
Symbol	Parameter	Test Conditions	V	Min	Тур	Max	Min	Max	Unit
V _{IH}	High-Level Input Voltage		2.0 3.0 3.6	1.5 2.0 2.4			1.5 2.0 2.4		V
V _{IL}	Low-Level Input Voltage		2.0 3.0 3.6			0.5 0.8 0.8		0.5 0.8 0.8	V
V _{OH}	High-Level Output Voltage (V _{in} = V _{IH} or V _{IL})	$I_{OH} = -50 \mu A$ $I_{OH} = -50 \mu A$ $I_{OH} = -4 \text{ mA}$	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		V
V _{OL}	Low-Level Output Voltage (V _{in} = V _{IH} or V _{IL})	$I_{OL} = 50 \mu A$ $I_{OL} = 50 \mu A$ $I_{OL} = 4 \text{ mA}$	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44	>
l _{in}	Input Leakage Current	$V_{in} = 5.5 \text{ V or GND}$	3.6			±0.1		±1.0	μΑ
l _{OZ}	Maximum 3-State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or GND}$	3.6			±0.2 5		±2.5	μΑ
I _{CC}	Quiescent Supply Current	$V_{in} = V_{CC}$ or GND	3.6			4.0		40.0	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns)

					A = 25°	С	$T_A = -40$	to 85°C	
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Propagation Delay LE to O	V _{CC} = 2.7 V	$C_L = 15 pF$ $C_L = 50 pF$		8.2 10.7	15.6 19.1	1.0 1.0	18.5 22.0	ns
		$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		6.4 8.9	10.1 13.6	1.0 1.0	12.0 15.5	
t _{PLH} , t _{PHL}	Propagation Delay D to O	V _{CC} = 2.7 V	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		7.6 10.1	14.5 18.0	1.0 1.0	17.5 21.0	ns
		$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		5.9 8.4	9.3 12.8	1.0 1.0	11.0 14.5	
t _{PZL} , t _{PZH}	Output Enable Time OE to O	$V_{CC} = 2.7 \text{ V}$ $R_L = 1 \text{ k}\Omega$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		7.8 10.3	15.0 18.5	1.0 1.0	18.5 22.0	ns
		$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_L = 1 \text{ k}\Omega$	$C_L = 15 pF$ $C_L = 50 pF$		6.1 8.6	9.7 13.2	1.0 1.0	12.0 15.5	
t _{PLZ} , t _{PHZ}	Output Disable Time OE to O	$V_{CC} = 2.7 \text{ V}$ $R_L = 1 \text{ k}\Omega$	$C_L = 50 pF$		12.1	19.1	1.0	22.0	ns
		$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_L = 1 \text{ k}\Omega$	C _L = 50 pF		10.1	13.6	1.0	15.5	
toshl toslh	Output-to-Output Skew (Note 1)	$V_{CC} = 2.7 \text{ V}$ $V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 50 \text{ pF}$ $C_L = 50 \text{ pF}$			1.5 1.5		1.5 1.5	ns

Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

CAPACITIVE CHARACTERISTICS

		T _A = 25°C		T _A = -40 to 85°C			
Symbol	Parameter	Min	Тур	Max	Min	Max	Unit
C _{in}	Input Capacitance		4	10		10	pF
C _{out}	Maximum 3–State Output Capacitance		6				pF
C _{PD}	Power Dissipation Capacitance (Note 2)		29				pF

^{2.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/8 (per latch). C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

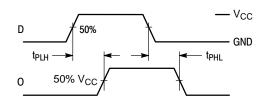
NOISE CHARACTERISTICS (Input t_r = t_f = 3.0 ns, C_L = 50 pF, V_{CC} = 3.3 V, Measured in SOIC Package)

		T _A = 25°C		
Symbol	Characteristic	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.5	0.8	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.5	-0.8	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

TIMING REQUIREMENTS (Input $t_r = t_f = 3.0 \text{ ns}$)

			T _A =	25°C	T _A = -40 to 85°C	
Symbol	Parameter	Test Conditions	Тур	Limit	Limit	Unit
t _{w(h)}	Minimum Pulse Width, LE	V _{CC} = 2.7 V V _{CC} = 3.3 ± 0.3 V		6.5 5.0	7.5 5.0	ns
t _{su}	Minimum Setup Time, D to LE	V _{CC} = 2.7 V V _{CC} = 3.3 ± 0.3 V		5.0 3.5	5.0 3.5	ns
t _h	Minimum Hold Time, D to LE	V _{CC} = 2.7 V V _{CC} = 3.3 ± 0.3 V		1.5 1.5	1.5 1.5	ns

SWITCHING WAVEFORMS



LE $t_{\rm W}$ $V_{\rm CC}$ $S_{\rm OW}$ $V_{\rm CC}$

Figure 2.

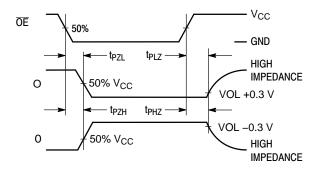
Figure 3.

 V_{CC}

GND

- V_{CC}

GND



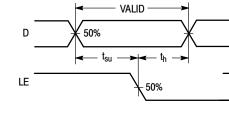
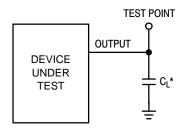
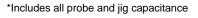


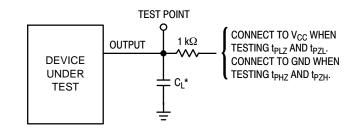
Figure 4.

Figure 5.

TEST CIRCUITS







*Includes all probe and jig capacitance

Figure 6. Propagation Delay Test Circuit

Figure 7. 3-State Test Circuit

ORDERING INFORMATION

Device	Package	Shipping †
MC74LVX573DWR2G	SOIC-20 (Pb-Free)	1000 / Tape & Reel
MC74LVX573DTG	TSSOP-20 (Pb-Free)	75 Units / Rail
MC74LVX573DTR2G	TSSOP-20 (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

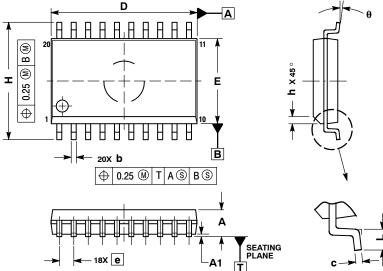




SOIC-20 WB CASE 751D-05 **ISSUE H**

DATE 22 APR 2015

SCALE 1:1



- DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS AND TOLERANCES.
- PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD
- PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL

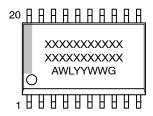
	MILLIMETERS					
DIM	MIN	MAX				
Α	2.35	2.65				
A1	0.10	0.25				
b	0.35	0.49				
С	0.23	0.32				
D	12.65	12.95				
E	7.40	7.60				
е	1.27	BSC				
Н	10.05	10.55				
h	0.25	0.75				
L	0.50	0.90				
A	0 °	7 °				

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot ΥY = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98ASB42343B	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.					
DESCRIPTION:	SOIC-20 WB		PAGE 1 OF 1				

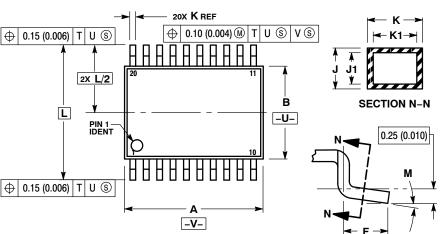
onsemi and ONSEMI. are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



TSSOP-20 WB CASE 948E ISSUE D

DATE 17 FEB 2016





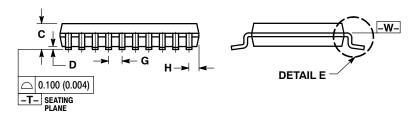
DETAIL E

NOTES:

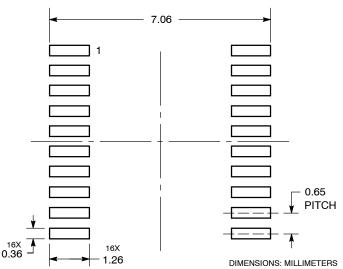
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
- (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-

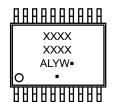
	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°



SOLDERING FOOTPRINT



GENERIC MARKING DIAGRAM*



= Assembly Location

= Wafer Lot = Year

= Work Week

= Pb-Free Package (Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■",

may or may not be present.

DOCUMENT NUMBER:	98ASH70169A	Electronic versions are uncontrolled except when accessed directly from the Document Repr Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	TSSOP-20 WB		PAGE 1 OF 1

ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales